



# HBC547

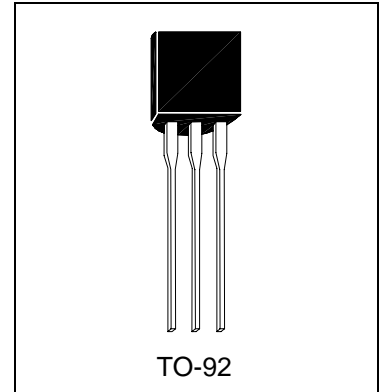
NPN EPITAXIAL PLANAR TRANSISTOR

## Description

The HBC547 is designed for use in driver stage of audio amplifier.

## Features

- High Breakdown Voltage: 45V
- High DC Current Gain: 110-800 at  $I_C=2mA$



## Absolute Maximum Ratings

- Maximum Temperatures
  - Storage Temperature ..... -55 ~ +150 °C
  - Junction Temperature ..... +150 °C Maximum
- Maximum Power Dissipation
  - Total Power Dissipation ( $T_A=25^{\circ}C$ ) ..... 625 mW
- Maximum Voltages and Currents ( $T_A=25^{\circ}C$ )
  - $V_{CBO}$  Collector to Base Voltage ..... 50 V
  - $V_{CEO}$  Collector to Emitter Voltage ..... 45 V
  - $V_{EBO}$  Emitter to Base Voltage ..... 6 V
  - $I_C$  Collector Current ..... 100mA

## Electrical Characteristics ( $T_A=25^{\circ}C$ )

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{CBO}$	50	-	-	V	$I_C=100\mu A, I_E=0$
$BV_{CEO}$	45	-	-	V	$I_C=1mA, I_B=0$
$BV_{EBO}$	6	-	-	V	$I_E=10\mu A, I_C=0$
$I_{CBO}$	-	-	15	nA	$V_{CB}=30V, I_E=0$
$V_{BE(on)1}$	0.58	-	0.7	V	$I_C=2mA, V_{CE}=5V$
$V_{BE(on)2}$	-	-	0.77	V	$I_C=10mA, V_{CE}=5V$
* $V_{BE(sat)1}$	-	0.7	-	V	$I_C=10mA, I_B=0.5mA$
* $V_{BE(sat)2}$	-	0.9	-	V	$I_C=100mA, I_B=5mA$
* $V_{CE(sat)1}$	-	-	0.25	V	$I_C=10mA, I_B=0.5mA$
* $V_{CE(sat)2}$	-	-	0.6	V	$I_C=100mA, I_B=5mA$
* $h_{FE}$	110	-	800		$V_{CE}=5V, I_C=2mA$
fT	-	300	-	MHZ	$V_{CE}=5V, I_C=10mA, f=100MHZ$
Cob	-	-	4.5	Pf	$V_{CE}=10V, I_E=0, f=1MHZ$

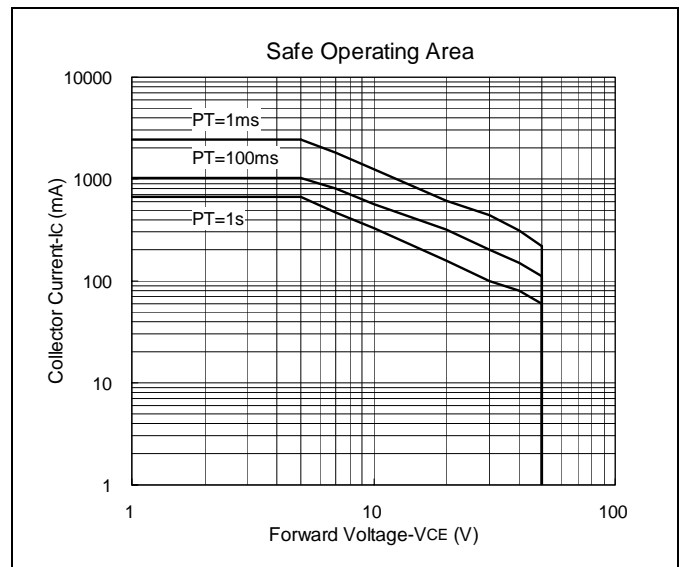
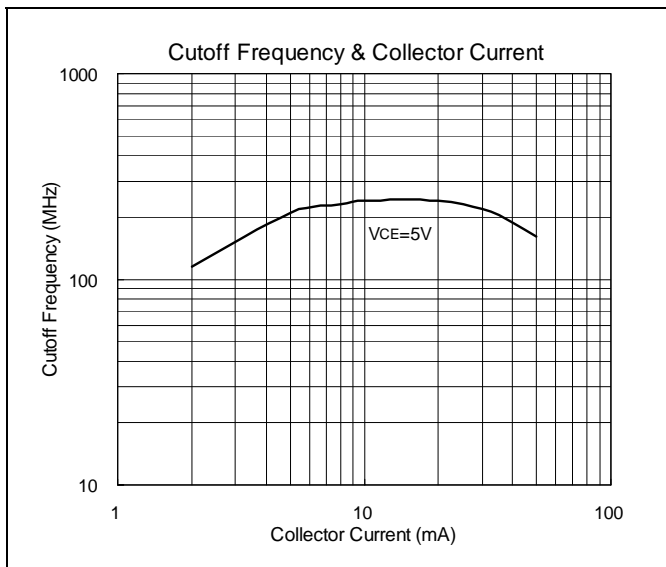
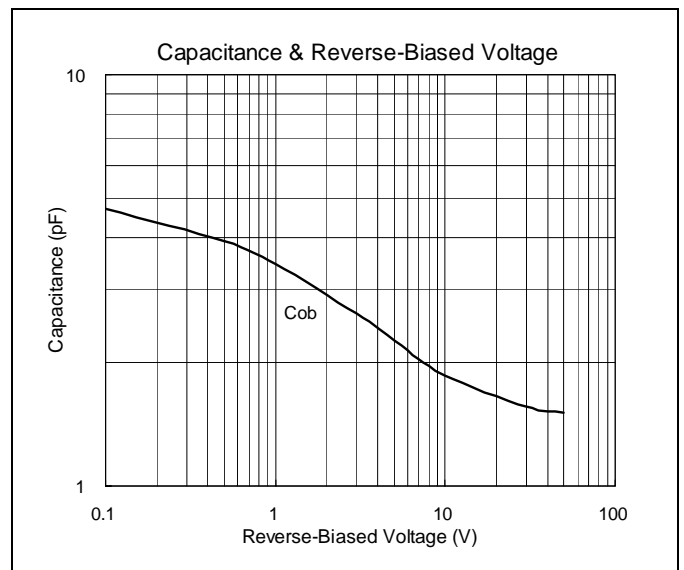
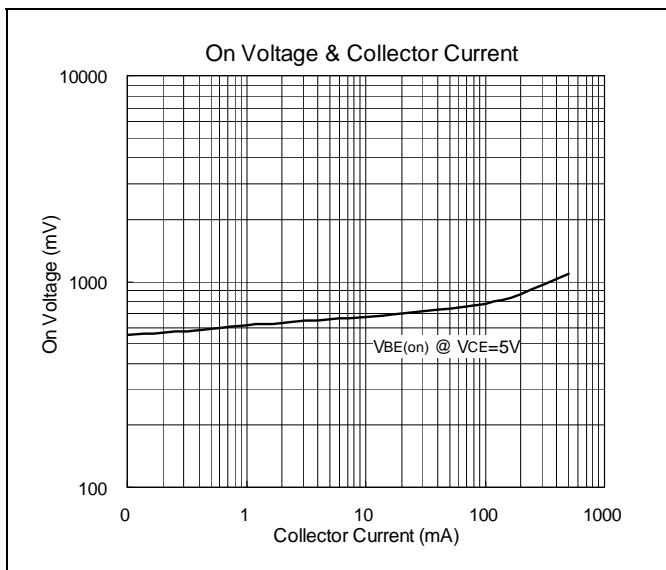
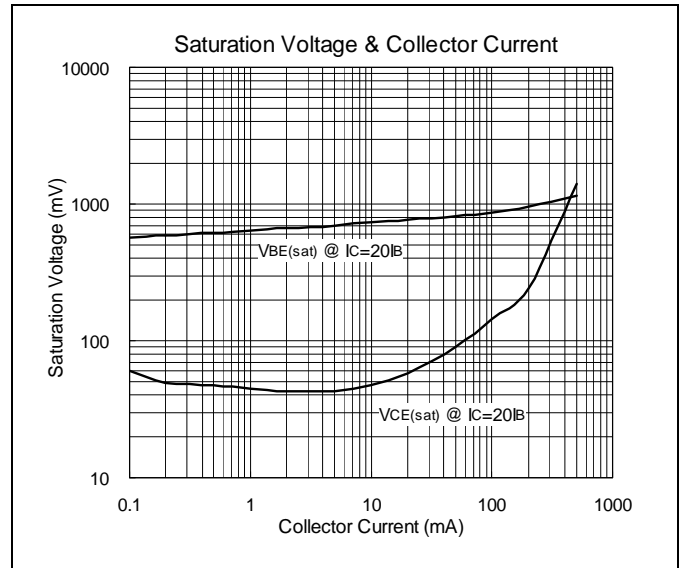
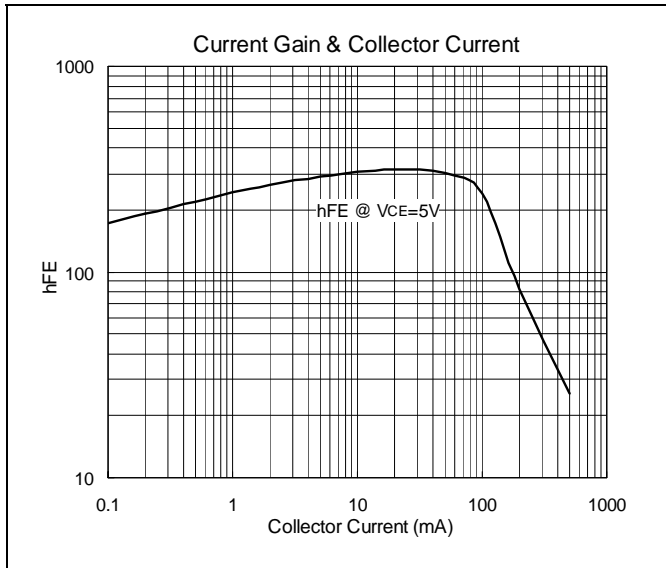
\*Pulse Test: Pulse Width  $\leq 380\mu s$ , Duty Cycle  $\leq 2\%$

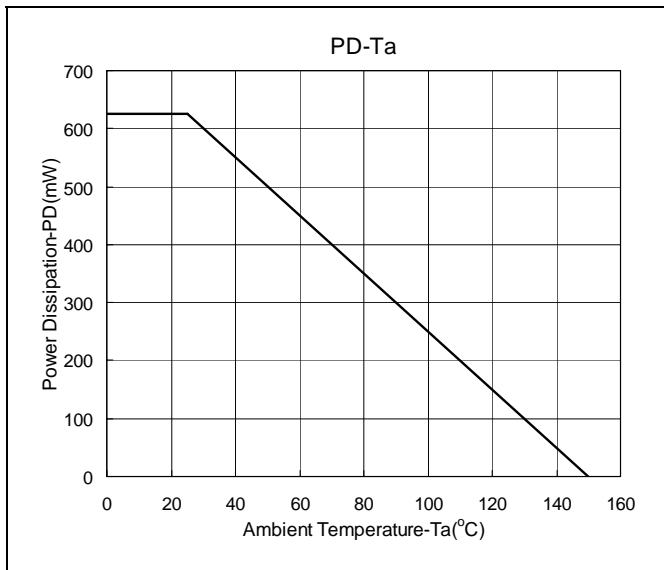
## Classification of hFE

Rank	A	B	C
Range	110-220	200-450	420-800



### Characteristics Curve







### TO-92 Dimension

**Marking:**

Pb Free Mark  
 Pb-Free: "●" (Note)  
 Normal: None

Date Code      Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Collector 2.Base 3.Emitter

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.33	4.83
B	4.33	4.83
C	12.70	-
D	0.36	0.56
E	-	*1.27
F	3.36	3.76
G	0.36	0.56
H	-	*2.54
I	-	*1.27
$\alpha 1$	-	*5°
$\alpha 2$	-	*2°
$\alpha 3$	-	*2°

\*: Typical, Unit: mm

3-Lead TO-92 Plastic Package  
 HSMC Package Code: A

### TO-92 Taping Dimension

DIM	Min.	Max.
A	4.33	4.83
D	3.80	4.20
D1	0.36	0.53
D2	4.33	4.83
F1,F2	2.40	2.90
H	15.50	16.50
H1	8.50	9.50
H2	-	1
H2A	-	1
H3	-	27
H4	-	21
L	-	11
L1	2.50	-
P	12.50	12.90
P1	5.95	6.75
P2	50.30	51.30
T	-	0.55
T1	-	1.42
T2	0.36	0.68
W	17.50	19.00
W1	5.00	7.00

Unit: mm

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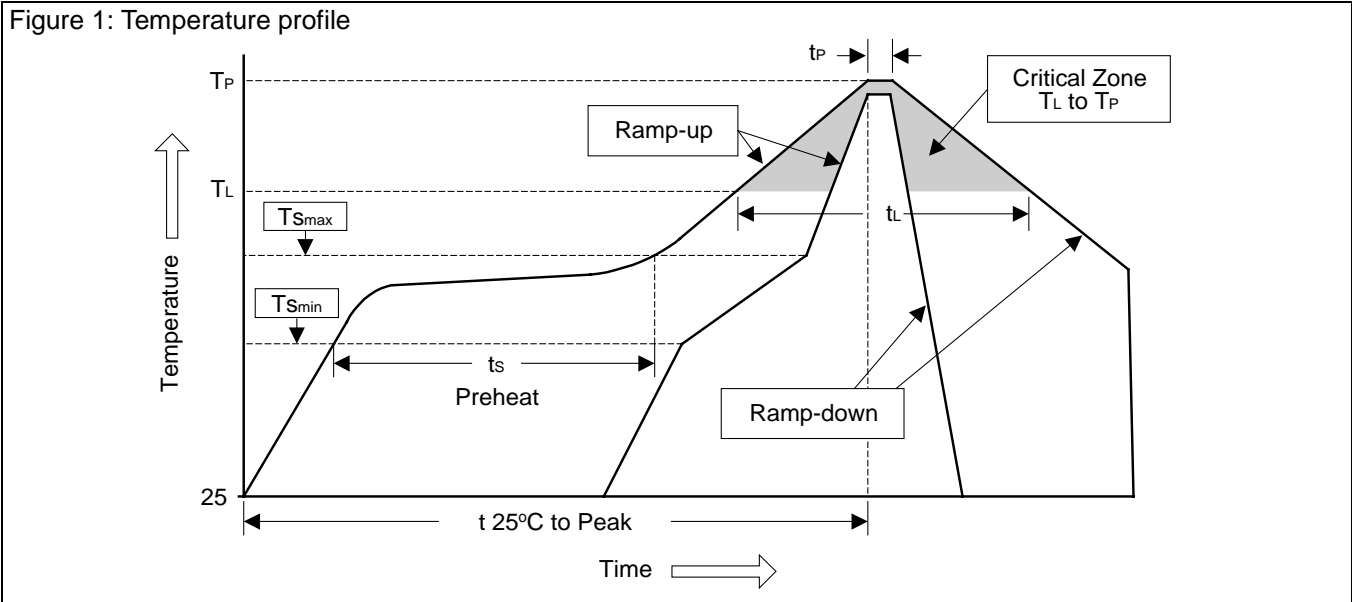
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### Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	$<3^{\circ}\text{C}/\text{sec}$	$<3^{\circ}\text{C}/\text{sec}$
Preheat		
- Temperature Min ( $T_{Smin}$ )	100°C	150°C
- Temperature Max ( $T_{Smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60~120 sec	60~180 sec
$T_{Smax}$ to $T_L$		
- Ramp-up Rate	$<3^{\circ}\text{C}/\text{sec}$	$<3^{\circ}\text{C}/\text{sec}$
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60~150 sec	60~150 sec
Peak Temperature ( $T_P$ )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	10~30 sec	20~40 sec
Ramp-down Rate	$<6^{\circ}\text{C}/\text{sec}$	$<6^{\circ}\text{C}/\text{sec}$
Time 25°C to Peak Temperature	$<6$ minutes	$<8$ minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec